

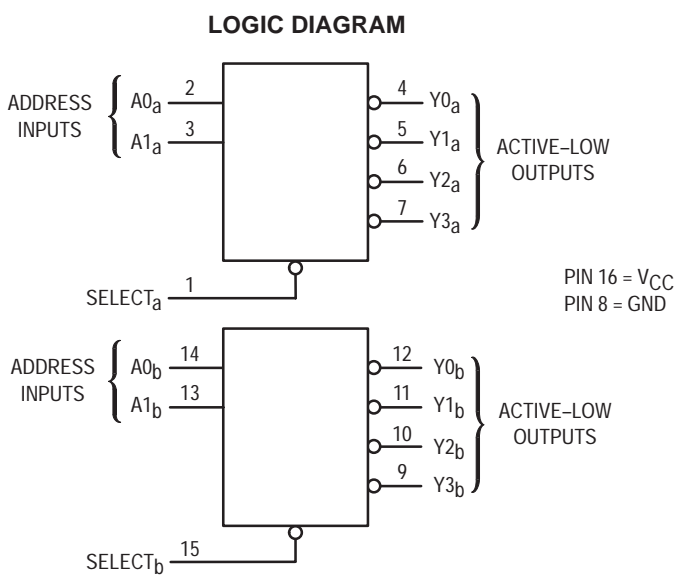
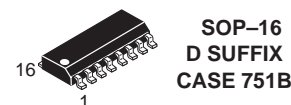
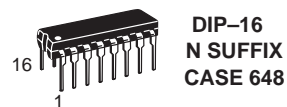
## Dual 1-of-4 Decoder/ Demultiplexer

### High-Performance Silicon-Gate CMOS

The 74HC139A is identical in pinout to the LS139. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of two independent 1-of-4 decoders, each of which decodes a two-bit Address to one-of-four active-low outputs. Active-low Selects are provided to facilitate the demultiplexing and cascading functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output, and utilizing the Select as a data input.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0  $\mu$ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 100 FETs or 25 Equivalent Gates

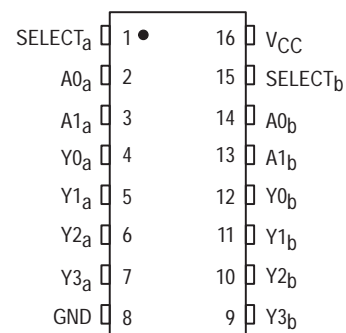


**FUNCTION TABLE**

Select	Inputs		Outputs			
	A1	A0	Y0	Y1	Y2	Y3
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L

X = don't care

### PIN ASSIGNMENT



### ORDERING INFORMATION

Device	Package	Shipping
74HC139N	DIP-16	2000 / Box
74HC139M/TR	SOP-16	2500 / Reel

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	- 1.5 to V <sub>CC</sub> + 1.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP† SOIC Package†	750 500	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

\*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	V <sub>CC</sub> = 2.0 V 0 V <sub>CC</sub> = 4.5 V 0 V <sub>CC</sub> = 6.0 V 0	1000 500 400	ns

### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				- 55 to 25°C	≤ 85°C	≤ 125°C	
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V  I <sub>out</sub>   ≤ 20 μA	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V <sub>IL</sub>	Maximum Low-Level Input Voltage	V <sub>out</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V  I <sub>out</sub>   ≤ 20 μA	2.0	0.5	0.5	0.5	V
			4.5	1.35	1.35	1.35	
			6.0	1.8	1.8	1.8	
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20 μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 4.0 mA  I <sub>out</sub>   ≤ 5.2 mA	4.5	3.98	3.84	3.70	
			6.0	5.48	5.34	5.20	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20 μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 4.0 mA  I <sub>out</sub>   ≤ 5.2 mA	4.5	0.26	0.33	0.40	
			6.0	0.26	0.33	0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0 μA	6.0	4	40	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

**AC ELECTRICAL CHARACTERISTICS** ( $C_L = 50$  pF, Input  $t_r = t_f = 6.0$  ns)

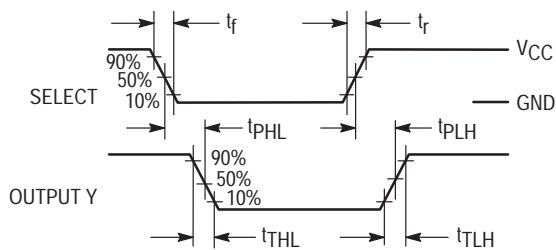
Symbol	Parameter	VCC V	Guaranteed Limit			Unit
			- 55 to 25°C	≤ 85°C	≤ 125°C	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Select to Output Y (Figures 1 and 3)	2.0	115	145	175	ns
		4.5	23	29	35	
		6.0	20	25	30	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 2 and 3)	2.0	115	145	175	ns
		4.5	23	29	35	
		6.0	20	25	30	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0	75	95	110	ns
		4.5	15	19	22	
		6.0	13	16	19	
C <sub>in</sub>	Maximum Input Capacitance	—	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

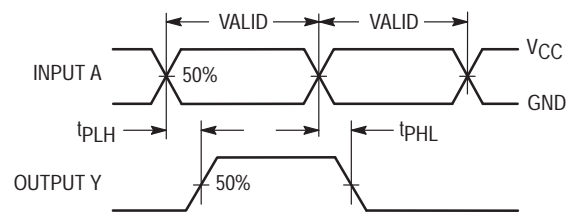
C <sub>PD</sub>	Power Dissipation Capacitance (Per Decoder)*	Typical @ 25°C, VCC = 5.0 V	
		55	pF

\* Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ . For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

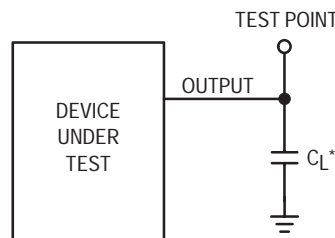
**SWITCHING WAVEFORMS**



**Figure 1.**



**Figure 2.**



\*Includes all probe and jig capacitance

**Figure 3. Test Circuit**

**PIN DESCRIPTIONS**

**ADDRESS INPUTS**

**A0<sub>a</sub>, A1<sub>a</sub>, A0<sub>b</sub>, A1<sub>b</sub> (Pins 2, 3, 14, 13)**

Address inputs. These inputs, when the respective 1-of-4 decoder is enabled, determine which of its four active-low outputs is selected.

**CONTROL INPUTS**

**Select<sub>a</sub>, Select<sub>b</sub> (Pins 1, 15)**

Active-low select inputs. For a low level on this input, the outputs for that particular decoder follow the Address

inputs. A high level on this input forces all outputs to a high level.

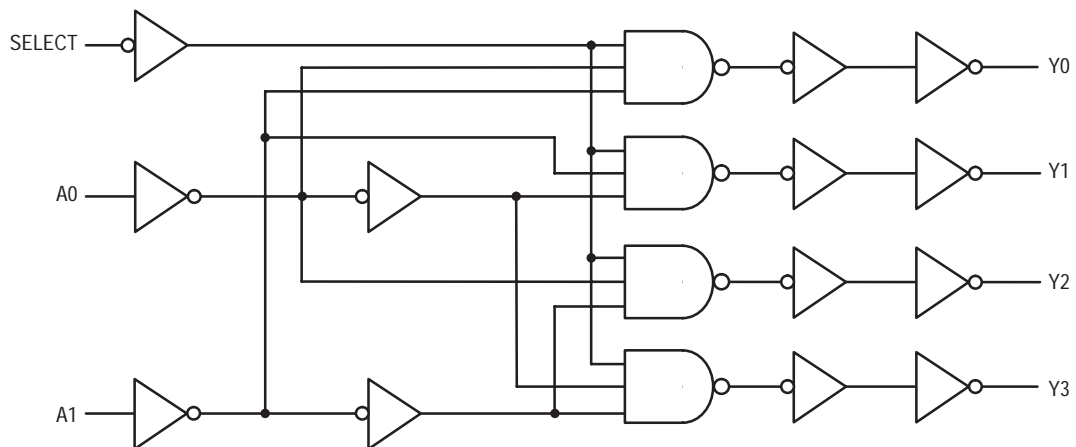
**OUTPUTS**

**Y0<sub>a</sub> – Y3<sub>a</sub>, Y0<sub>b</sub> – Y3<sub>b</sub> (Pins 4 – 7, 12, 11, 10, 9)**

Active-low outputs. These outputs assume a low level when addressed and the appropriate Select input is active. These outputs remain high when not addressed or the appropriate Select input is inactive.

**EXPANDED LOGIC DIAGRAM**

**(1/2 OF DEVICE)**



### Important statement:

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